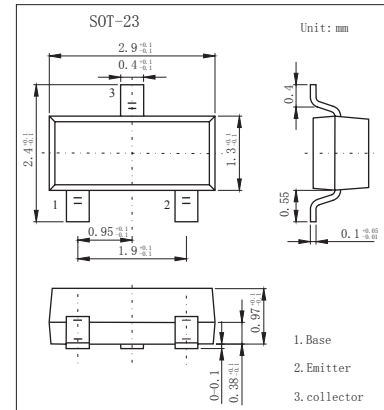


PNP Transistors

KST8550D

■ Features

- Collector Current: $I_c = -1.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-40	V
Collector-Emitter Voltage	V_{CE0}	-25	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current -Continuous	I_c	-1.5	A
Collector Power Dissipation	P_c	0.3	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CE0}	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cut-off current	I_{cBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{cEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{eBO}	$V_{EB} = -5V, I_c = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_c = -100mA$	120		400	
		$V_{CE} = -1V, I_c = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -800mA, I_B = -80mA$			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_c = -1V, V_{CE} = -10mA$			-1	V
output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Transition frequency	f_T	$V_{CE} = -10V, I_c = -50mA, f = 30MHz$	100			MHz

■ h_{FE} Classification

Marking	Y2

KST8550D

Typical Characteristics

